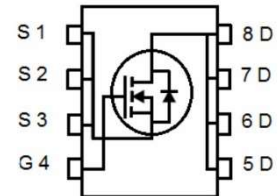




1. Description

SS010N03NSL, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

Schematic Diagram



KEY CHARACTERISTICS

Parameter	Value	Unit
V _{DSS}	30	V
I _D	200	A
R _{DS(on)} .typ	0.8	mΩ

FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 1\text{m}\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS010N03NSL	PDFN5X6	SS010N03NSL	Reel

PDFN5x6

